

TOSHIBA Transistor Silicon NPN Triple Diffused Type

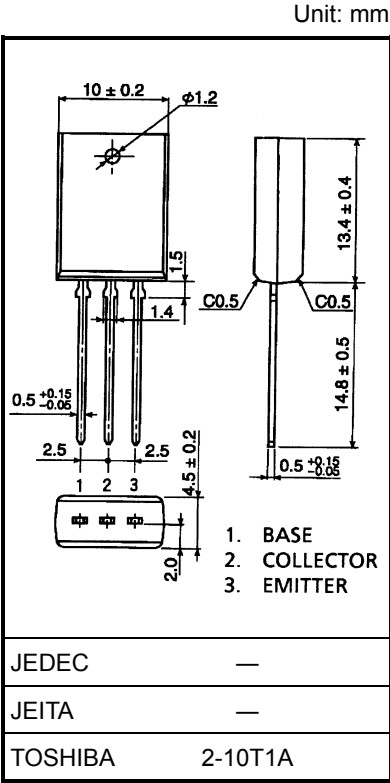
2SD2525

Audio Frequency Power Amplifier Applications

- High DC current gain: 100 (min)
- Low saturation voltage: $V_{CE(sat)} = 0.4\text{ V (typ.)}$ ($I_C = 2\text{ A}$, $I_B = 0.2\text{ A}$)
- Complementary to 2SB1640

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	60	V
Collector-emitter voltage		V_{CEO}	60	V
Emitter-base voltage		V_{EBO}	7	V
Collector current	DC	I_C	3	A
	Pulse	I_{CP}	6	
Base current		I_B	0.5	A
Collector power dissipation		P_C	1.8	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

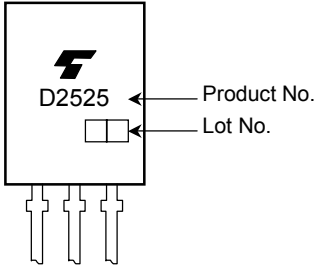


Weight: 1.5 g (typ.)

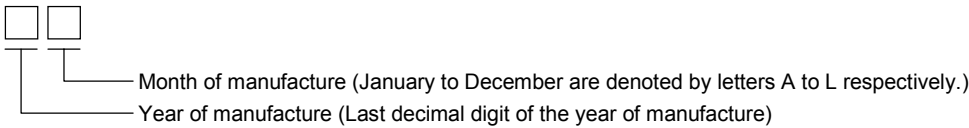
Electrical Characteristics (Ta = 25°C)

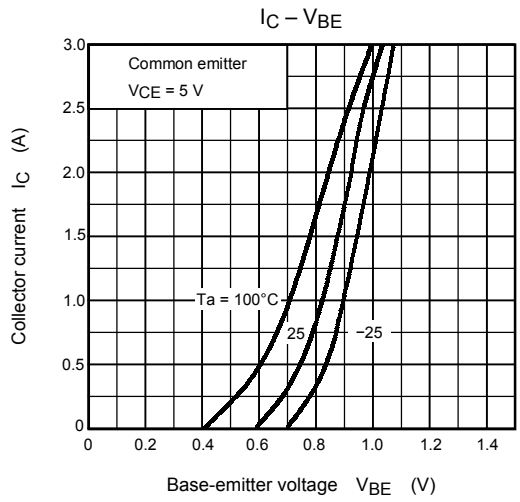
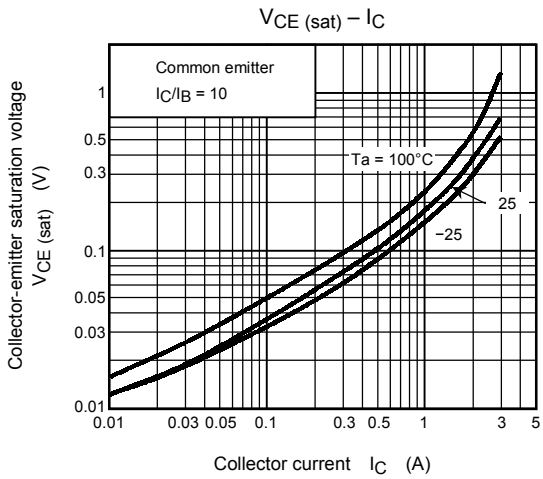
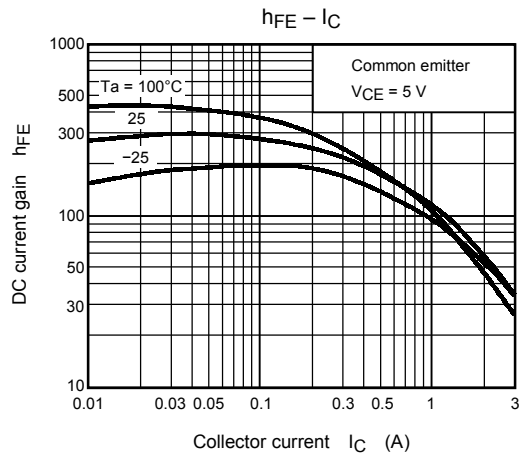
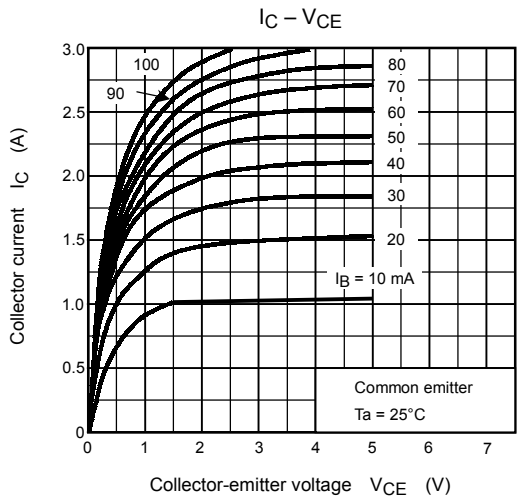
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	ICBO	V _{CB} = 60 V, I _E = 0	—	—	10	μA
Emitter cut-off current	IEBO	V _{EB} = 7 V, I _C = 0	—	—	10	μA
Collector-emitter breakdown voltage	V _(BR) CEO	I _C = 50 mA, I _B = 0	60	—	—	V
DC current gain	h _{FE} (1)	V _{CE} = 5 V, I _C = 0.5 A	100	—	320	
	h _{FE} (2)	V _{CE} = 5 V, I _C = 2 A	20	—	—	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 2 A, I _B = 0.2 A	—	0.4	1.0	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 0.5 A	—	0.75	1.0	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 0.5 A	—	3	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	—	35	—	pF

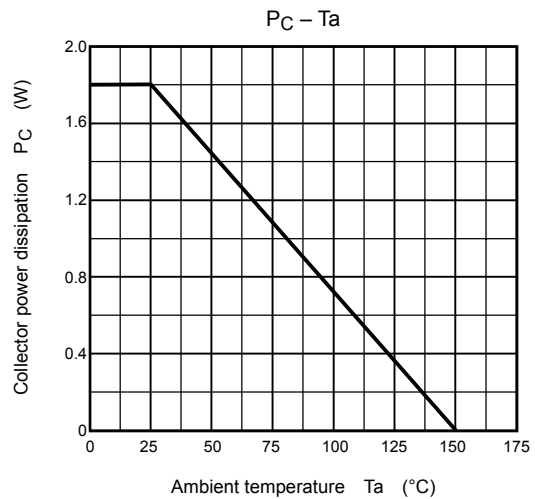
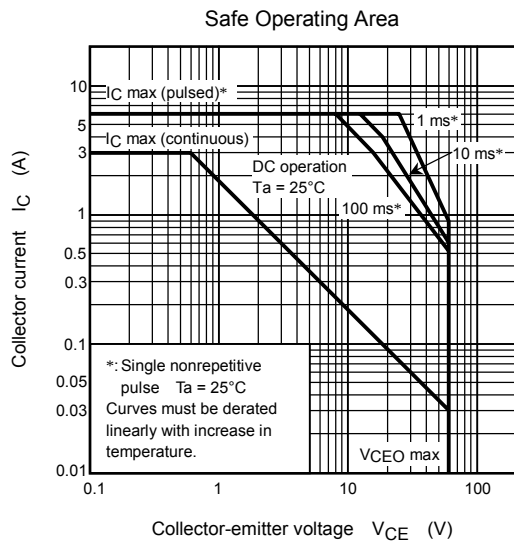
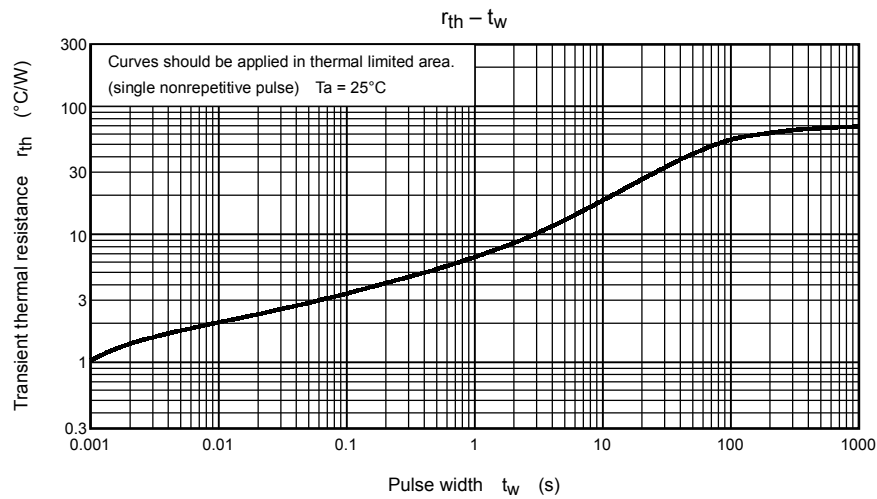
Marking



Explanation of Lot No.







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